IN THE CLAIMS

Claims 1-2 (Cancelled)

3. (Previously Presented) A magnetic memory device constructed as a magnetic random access memory, said magnetic memory device comprising:

a memory element having a magnetization pinned layer in which the orientation of magnetization is pinned, and a magnetic layer in which the orientation of magnetization is changeable; and

a magnetic shield layer for magnetically shielding said memory element, said memory element disposed so as to avoid an edge portion and a center portion of said magnetic shield layer;

wherein said memory element is disposed in a region between a position at 0.1 L inward from one side of said magnetic shield layer and a position at 0.15 L outward from the center of said magnetic shield layer toward one side thereof, where a length from one side of said magnetic shield layer to an opposed side thereof is L.

4. (Previously Presented) A memory device according to claim ~~3 or 11~~, wherein said memory element is disposed in a region between a position at 0.2 L inward from said one side and a position at 0.15 L outward from the center of said shield layer toward said one side thereof, where said magnetic shield layer is provided on both sides of said memory element, and a distance between said magnetic shield layers, a length from said one side of said magnetic shield layer to the opposed side thereof, and an external magnetic field to be applied are constant respectively.

5. (Previously Presented) A memory device according to claim ~~3 or 11~~, wherein said memory element is disposed in a region between a position at 0.1 L inward from said one side thereof and a position at 0.2 L outward from the center of the shield layer toward said one side thereof, where a distance between said magnetic shield layers, a thickness of said magnetic shield layers, and an external magnetic field to be applied are constant respectively.

Claims 6-8 (Cancelled)

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9. (Previously Presented) A magnetic memory device constructed as a magnetic random access memory, said magnetic memory device comprising:

a memory element having a magnetization pinned layer in which the orientation of magnetization is pinned, and a magnetic layer in which the orientation of magnetization is changeable; and

a magnetic shield layer for magnetically shielding said memory element, said memory element disposed so as to avoid an edge portion and a center portion of said magnetic shield layer;

wherein said magnetic shield layer is disposed on the top and/or bottom of a package having by sealing said memory element therein, or/and on the upper portion and/or the lower portion of said memory element within said package, and wherein said magnetic shield layer is formed of soft magnetic material that exhibits saturation magnetism at 1.8 tesla or more.

10. (Cancelled)

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11. (Previously Presented) A magnetic memory device comprising:

a memory element having a magnetic layer capable of being magnetized; and

a magnetic shield layer for magnetically shielding said memory element;

wherein said memory element is disposed so as to avoid an edge portion and a center portion of said magnetic shield layer, and wherein said memory element is disposed in a region between a position at 0.1 L inward from one side of said magnetic shield layer and a position at 0.15 L outward from the center of said magnetic shield layer toward one side thereof, where a length from one side of said magnetic shield layer to an opposed side thereof is L.

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12. (Previously Presented) A magnetic memory device comprising:

a memory element having a magnetic layer capable of being magnetized; and

a magnetic shield layer for magnetically shielding said memory element;

wherein said memory element is disposed so as to avoid an edge portion and a center portion of said magnetic shield layer, wherein said magnetic shield layer is disposed on the top and/or bottom of a package having by sealing said memory element therein, or/and on the upper

portion and/or the lower portion of said memory element within said package, and wherein said magnetic shield layer is formed of soft magnetic material that exhibits saturation magnetism at 1.8 tesla or more.